

ABSTRACT

A photodetector formed in monolithic form including a first active area of doped single-crystal silicon corresponding to first and second photodiodes having the same surface area as two charge transfer MOS transistors, and as one storage diode; a second
5 active area of doped single-crystal silicon arranged next to the portion of the first active area associated with the second photodiode and corresponding to a precharge switch; and a third active doped single-crystal silicon area arranged next to the portion of the first active area associated with the first photodiode and corresponding to two read MOS transistors in series, in which the surfaces of the second and third active areas exposed to
10 light are substantially identical.